

Title (en)
SEMICONDUCTOR DEVICE

Title (de)
HALBLEITERBAUELEMENT

Title (fr)
DISPOSITIF SEMI-CONDUCTEUR

Publication
EP 2698823 A1 20140219 (EN)

Application
EP 12770971 A 20120413

Priority
• JP 2011091332 A 20110415
• JP 2012002597 W 20120413

Abstract (en)
A semiconductor device includes a substrate, a channel layer that is formed above the substrate, where the channel layer is made of a first nitride series compound semiconductor, a barrier layer that is formed on the channel layer, a first electrode that is formed on the barrier layer, and a second electrode that is formed above the channel layer. Here, the barrier layer includes a block layers and a quantum level layer. The block layer is formed on the channel layer and made of a second nitride series compound semiconductor having a larger band gap energy than the first nitride series compound semiconductor, and the quantum level layer is made of a third nitride series compound semiconductor having a smaller band gap energy than the second nitride series compound semiconductor, and has a quantum level formed therein.

IPC 8 full level
H01L 21/02 (2006.01); **H01L 21/205** (2006.01); **H01L 21/338** (2006.01); **H01L 29/06** (2006.01); **H01L 29/15** (2006.01); **H01L 29/47** (2006.01); **H01L 29/778** (2006.01); **H01L 29/812** (2006.01); **H01L 29/872** (2006.01)

CPC (source: EP KR US)
H01L 21/0237 (2013.01 - EP US); **H01L 21/02381** (2013.01 - EP US); **H01L 21/02458** (2013.01 - EP US); **H01L 21/02507** (2013.01 - EP US); **H01L 21/0254** (2013.01 - EP US); **H01L 21/0262** (2013.01 - EP US); **H01L 21/18** (2013.01 - KR); **H01L 29/1029** (2013.01 - EP US); **H01L 29/155** (2013.01 - EP US); **H01L 29/778** (2013.01 - KR); **H01L 29/7783** (2013.01 - EP US); **H01L 29/7787** (2013.01 - EP US); **H01L 29/812** (2013.01 - EP US); **H01L 29/872** (2013.01 - EP KR US); **H01L 29/2003** (2013.01 - EP US)

Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

DOCDB simple family (publication)
US 2014008615 A1 20140109; CN 103348479 A 20131009; EP 2698823 A1 20140219; EP 2698823 A4 20141001; JP 2012227227 A 20121115; KR 20140042770 A 20140407; WO 2012140915 A1 20121018

DOCDB simple family (application)
US 201313952640 A 20130728; CN 201280007853 A 20120413; EP 12770971 A 20120413; JP 2011091332 A 20110415; JP 2012002597 W 20120413; KR 20137018278 A 20120413